Designer's™ Data Sheet

SWITCHMODETM

NPN Bipolar Power Transistor For Switching Power Supply Applications

The MJE/MJF18006 have an applications specific state-of-the-art die designed for use in 220 V line-operated Switchmode Power supplies and electronic light ballasts. These high voltage/high speed transistors offer the following:

- Improved Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain hff
 - Fast Switching
 - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot-to-Lot
- Two Package Choices: Standard TO–220 or Isolated TO–220
- MJF18006, Case 221D, is UL Recognized at 3500 V_{RMS}: File #E69369

MAXIMUM RATINGS

Rating	Symbol	MJE18006	MJF18006	Unit
Collector–Emitter Sustaining Voltage	VCEO	450		Vdc
Collector–Emitter Breakdown Voltage	VCES	10	Vdc	
Emitter–Base Voltage	V _{EBO}	9.	0	Vdc
Collector Current — Continuous — Peak(1)	I _C	6.0 15		Adc
Base Current — Continuous — Peak(1)	I _B I _{BM}	4. 8.	Adc	
RMS Isolation Voltage(2) Test No. 1 Per Fig. 22a (for 1 sec, R.H. < 30%, Test No. 1 Per Fig. 22b $T_C = 25^{\circ}C$) Test No. 1 Per Fig. 22c	VISOL	_ _ _	4500 3500 1500	Volts
Total Device Dissipation (T _C = 25°C) Derate above 25°C	PD	100 0.8	40 0.32	Watts W/°C
Operating and Storage Temperature	TJ, T _{stg}	−65 to	o 150	°C

THERMAL CHARACTERISTICS

Rating	Symbol	MJE18006	MJF18006	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{ hetaJC}$	1.25 62.5	3.125 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	26	00	ç

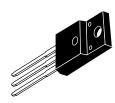
MJE18006* MJF18006*

*Motorola Preferred Device

POWER TRANSISTOR 6.0 AMPERES 1000 VOLTS 40 and 100 WATTS



CASE 221A-06 TO-220AB MJE18006



CASE 221D-02 ISOLATED TO-220 TYPE UL RECOGNIZED MJF18006

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (I _C = 100 mA, L = 25 mH)	V _{CEO(sus)}	450	_		Vdc
Collector Cutoff Current (V _{CE} = Rated V _{CEO} , I _B = 0)	ICEO	_	_	100	μAdc
Collector Cutoff Current (V _{CE} = Rated V _{CES} , V _{EB} = 0)	ICES	_	_	100	μAdc
$(T_{C} = 125^{\circ}C)$		_	l –	500	
$(V_{CE} = 800 \text{ V}, V_{EB} = 0)$ $(T_{C} = 125^{\circ}C)$		_	_	100	
Emitter Cutoff Current (V _{EB} = 9.0 Vdc, I _C = 0)	I _{EBO}	_		100	μAdc

⁽¹⁾ Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

(continued)

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Preferred devices are Motorola recommended choices for future use and best overall value.

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REV 1



⁽²⁾ Proper strike and creepage distance must be provided.

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ELECTRICAL CHARACTERISTICS — **continued** ($T_C = 25$ °C unless otherwise specified)

	С	haracteristic			Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS									
Base–Emitter Saturation Voltage ($I_C = 1.3 \text{ Adc}$, $I_B = 0.13 \text{ Adc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 0.6 \text{ Adc}$)					V _{BE(sat)}	_ _	0.83 0.94	1.2 1.3	Vdc
Collector–Emitter Satura (IC = 1.3 Adc, I _B = 0.13		tage		(To = 125°C)	VCE(sat)	_	0.25	0.6 0.65	Vdc
$(I_C = 3.0 \text{ Adc}, I_B = 0.6)$	Adc)			$(T_C = 125^{\circ}C)$ $(T_C = 125^{\circ}C)$		_ _ _	0.27 0.35 0.4	0.03 0.7 0.8	
DC Current Gain (I _C = 0.	5 Adc,	V _{CE} = 5.0 Vdc)			hFE	14	_	34	_
(I _C = 3.	0 Adc,	V _{CE} = 1.0 Vdc)		$(T_C = 125^{\circ}C)$ $(T_C = 125^{\circ}C)$		— 6.0 5.0	32 10 8.0	_ _ _	
		V _{CE} = 1.0 Vdc) v, V _{CE} = 5.0 Vdc)	(T _C	= 25 to 125°C)		11 10	17 22	_ _	
DYNAMIC CHARACTERIS									
Current Gain Bandwidth				O MHz)	fT	_	14	_	MHz
Output Capacitance (VCI	B = 10	Vdc, IE = 0, f = 1.0	MHz)		C _{ob}	_	75	120	pF
Input Capacitance (VEB	= 8.0 V	")			C _{ib}		1000	1500	pF
Dynamic Saturation Volta Determined 1.0 μs and	-	$(I_C = 1.3 \text{ Adc})$ $I_{B1} = 130 \text{ mAdc}$ $V_{CC} = 300 \text{ V})$	1.0 µs	(T _C = 125°C)	VCE(dsat)	<u> </u>	5.5 12		Volts
3.0 μs respectively after rising I _{B1} reaches 90%	er		3.0 μs	(T _C = 125°C)			3.0 7.0		
final I _{B1} (see Figure 18)		(I _C = 3.0 Adc I _{B1} = 0.6 Adc V _{CC} = 300 V)	1.0 μs	(T _C = 125°C)			9.5 14.5		
			3.0 μs	(T _C = 125°C)		_ _	2.0 7.5	_ _	
SWITCHING CHARACTE	RISTIC	S: Resistive Load	I (D.C. ≤	10%, Pulse Width	n = 20 μs)				
Turn-On Time		= 3.0 Adc, I _{B1} = 0 = 1.5 Adc, V _{CC} =		(T _C = 125°C)	t _{on}	_ _	90 100	180 —	ns
Turn-Off Time				(T _C = 125°C)	^t off	_ _	1.7 2.1	2.5 —	μs
Turn-On Time		= 1.3 Adc, I _{B1} = 0. = 0.65 Adc, V _{CC} =		(T _C = 125°C)	^t on	_ _	200 130	300 —	ns
Turn–Off Time				(T _C = 125°C)	^t off	_ _	1.2 1.5	2.5 —	μs
SWITCHING CHARACTE	RISTIC	S: Inductive Load	I (V _{clamp}	= 300 V, V _{CC} = 1	5 V, L = 200 μl	H)			
Fall Time	(IC =	= 1.5 Adc, I _{B1} = 0. I _{B2} = 0.65 Adc)		(T _C = 125°C)	tfi	_ _	100 120	180 —	ns
Storage Time	$(T_C = 125^{\circ}C)$ $(T_C = 125^{\circ}C)$			(T _C = 125°C)	t _{Si}	_ _	1.5 1.9	2.5 —	μs
Crossover Time				t _C	_ _	220 230	350 —	ns	
Fall Time	$(I_C = 3.0 \text{ Adc}, I_{B1} = 0.6 \text{ Adc}, I_{B2} = 1.5 \text{ Adc})$ $(T_C = 125^{\circ}C)$			t _{fi}	_ _	85 120	150 —	ns	
Storage Time	(T _C = 125°C)			t _{si}	_ _	2.15 2.75	3.2 —	μs	
Crossover Time	(T _C = 125°C)			t _C	_ 	200 310	300 —	ns	

TYPICAL STATIC CHARACTERISTICS

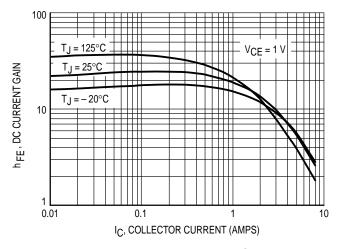


Figure 1. DC Current Gain @ 1 Volt

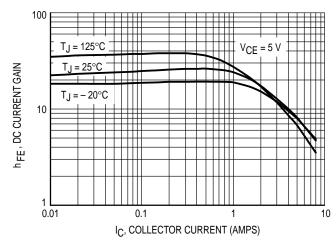


Figure 2. DC Current Gain @ 5 Volts

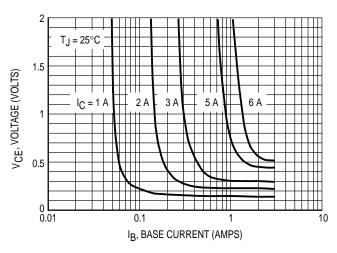


Figure 3. Collector Saturation Region

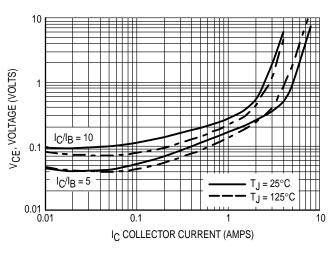


Figure 4. Collector-Emitter Saturation Voltage

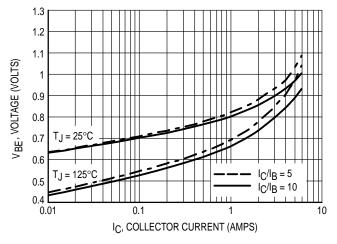


Figure 5. Base-Emitter Saturation Region

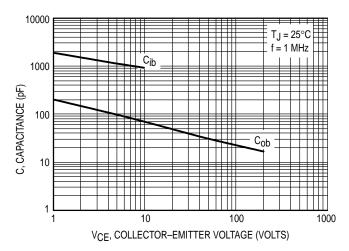


Figure 6. Capacitance

TYPICAL SWITCHING CHARACTERISTICS (IB2 = IC/2 for all switching)

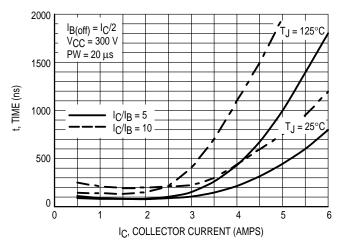


Figure 7. Resistive Switching, ton

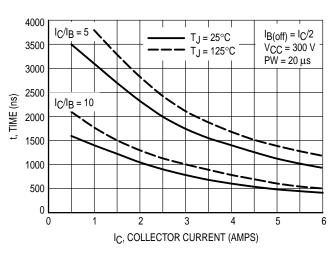


Figure 8. Resistive Switching, toff

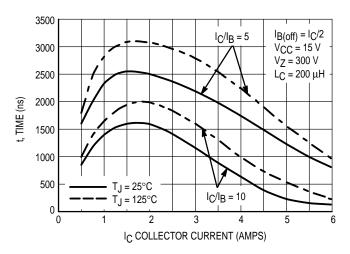


Figure 9. Inductive Storage Time, tsi

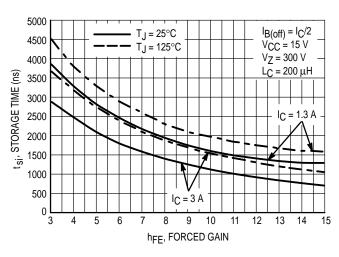


Figure 10. Inductive Storage Time, tsi(hFE)

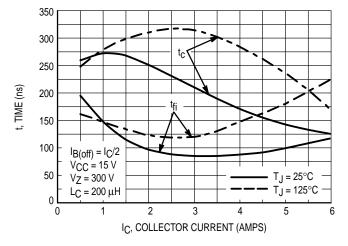


Figure 11. Inductive Switching, t_C and t_{fi} $I_C/I_B = 5$

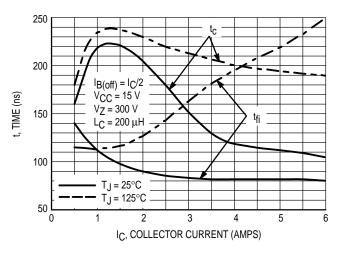
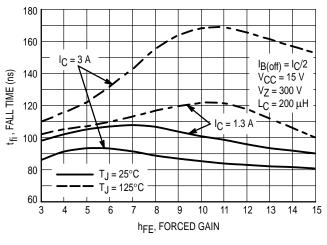


Figure 12. Inductive Switching, t_C and t_{fi} $I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS (IB2 = IC/2 for all switching)

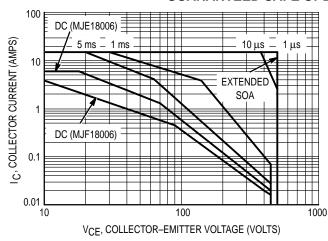


IB(off) = IC/2IC = 3 AV_{CC} = 15 V 300 $V_Z = 300 \text{ V}$ T_C, CROSSOVER TIME (ns) $L_{C} = 200 \, \mu H$ 250 200 $I_{C} = 1.3 A$ 150 100 T_J = 25°C T_J = 125°C 50 13 3 15 hFF, FORCED GAIN

Figure 13. Inductive Fall Time

Figure 14. Inductive Crossover Time

GUARANTEED SAFE OPERATING AREA INFORMATION



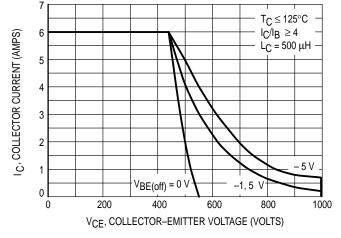


Figure 15. Forward Bias Safe Operating Area

Figure 16. Reverse Bias Switching Safe Operating Area

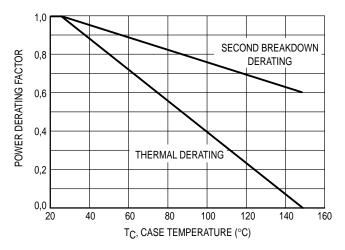
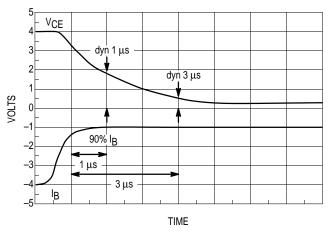


Figure 17. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on TC = 25°C; T_{J(pk)} is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \ge 25^{\circ}C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown in Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17. T_{J(pk)} may be calculated from the data in Figure 20 and 21. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base-to-emitter junction reverse-biased. The safe level is specified as a reversebiased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

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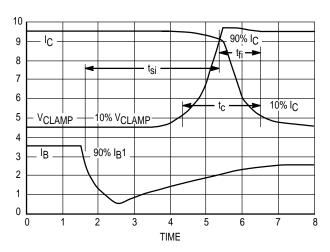


Figure 19. Inductive Switching Measurements

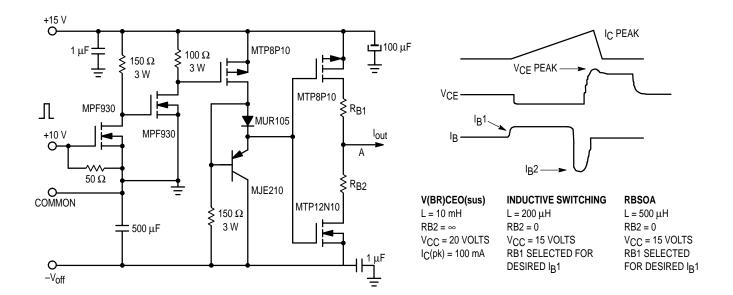


Table 1. Inductive Load Switching Drive Circuit

TYPICAL THERMAL RESPONSE

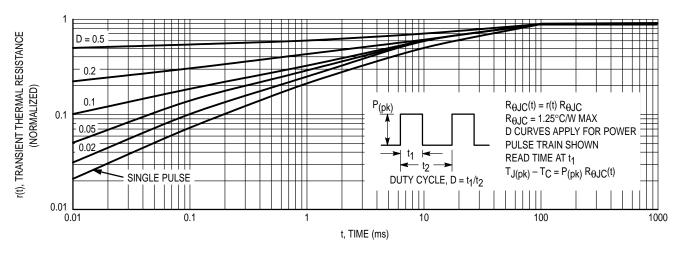


Figure 20. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18006

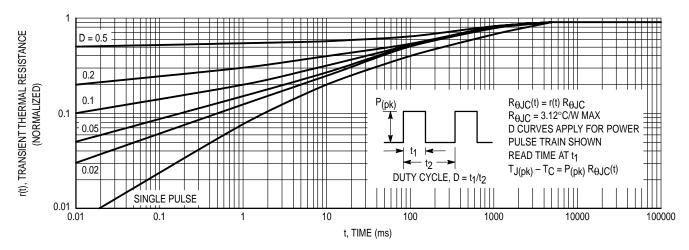
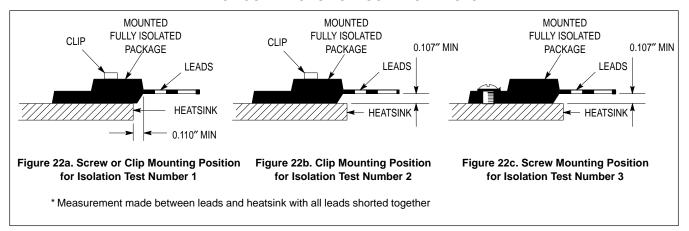


Figure 21. Typical Thermal Response (Z₀JC(t)) for MJF18006

TEST CONDITIONS FOR ISOLATION TESTS*



MOUNTING INFORMATION**

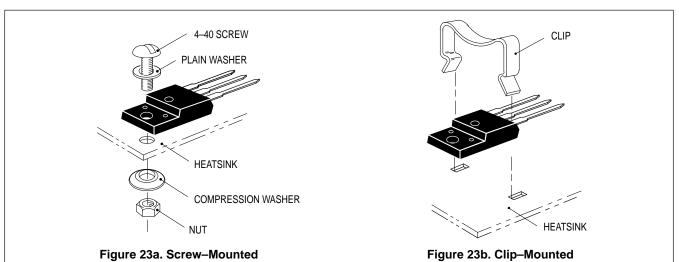


Figure 23. Typical Mounting Techniques for Isolated Package

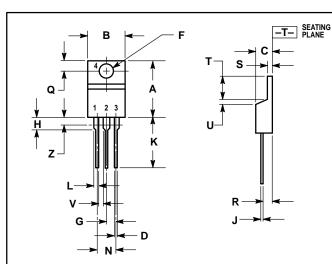
Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS



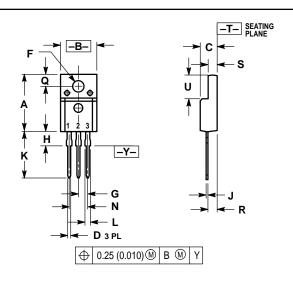
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

- PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.621	0.629	15.78	15.97	
В	0.394	0.402	10.01	10.21	
С	0.181	0.189	4.60	4.80	
D	0.026	0.034	0.67	0.86	
F	0.121	0.129	3.08	3.27	
G	0.100	BSC	2.54 BSC		
Н	0.123	0.129	3.13	3.27	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.14	1.52	
N	0.200	BSC	5.08	BSC	
Q	0.126	0.134	3.21	3.40	
R	0.107	0.111	2.72	2.81	
S	0.096	0.104	2.44	2.64	
U	0.259	0.267	6.58	6.78	

- STYLE 2: PIN 1. BASE
 - 2. COLLECTOR 3. EMITTER

CASE 221D-02 (ISOLATED TO-220 TYPE) **UL RECOGNIZED: FILE #E69369 ISSUE D**

MJE18006 MJF18006

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